CLL3595

SURFACE MOUNT
LOW LEAKAGE SILICON DIODE



SOD-80 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CLL3595 type is an epitaxial planar silicon diode, manufactured in a hermetically sealed glass surface mount package, designed for low leakage, high conductance applications.

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	150	V
Peak Working Reverse Voltage	V_{RWM}	125	V
Average Forward Current	I_O	150	mA
Forward Steady-State Current	I_F	225	mA
Recurrent Peak Forward Current	i_f	600	mA
Peak Forward Surge Current (1.0s pulse)	I_{FSM}	500	mA
Peak Forward Surge Current (1.0μs pulse)	I_{FSM}	4.0	A
Power Dissipation	P_D	500	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +200	°C
Thermal Resistance	Θ_{JA}	350	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
BV_R	I_R=100μA	150		V
I_R	V_R=125V		1.0	nA
I_R	V_R=125V, T_A=125°C		500	nA
I_R	V_R=125V, T_A=150°C		3.0	μA
I_R	V_R=30V, T_A=125°C		300	nA
V_F	I_F=1.0mA	0.54	0.69	V
V_F	I_F=5.0mA	0.62	0.77	V
V_F	I_F=10mA	0.65	0.80	V
V_F	I_F=50mA	0.75	0.88	V
V_F	I_F=100mA	0.79	0.92	V
V_F	I_F=200mA	0.83	1.00	V
C_T	V_R=0, f=1.0MHz		8.0	pF
t_{rr}	V_R=3.5V, I_f=10mA, R_L=1.0kΩ		3.0	μs

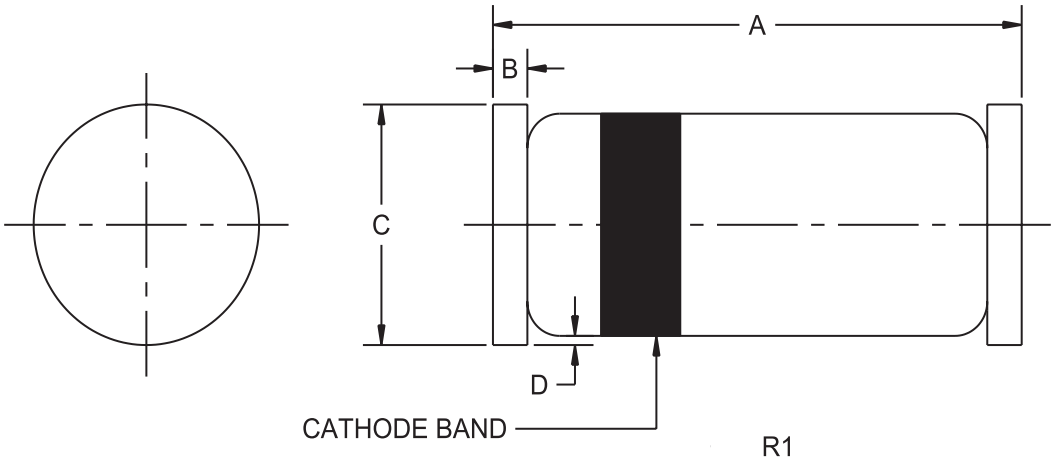
R1 (25-September 2001)

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SOD-80 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.130	0.146	3.30	3.71
B	0.016		0.41	
C (DIA)	0.051	0.067	1.30	1.70
D	-	0.004	-	0.10

SOD-80 (REV:R1)

R1 (25-September 2001)